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Substitute for form 1449B/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

Date Submitted: April 12, 2004

(use as many sheets as necessary)

**Complete if Known**

Application Number	Unassigned 10/821 921
Filing Date	04/12/2004
First Named Inventor	Yuichi OSHIMA
Group Art Unit	2811
Examiner Name	Unassigned
Attorney Docket Number	035532-0141

Sheet 1 of 1

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
DS	A1	2002/0197825	A1	USUI ET AL.	12-26-2002	
DS	A2	6,555,845	B2	SUNAKAWA ET AL.	04-29-2003	

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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
DS	A3	JP	2003-178984	A	NEC CORP., ET AL.	06-27-2003		Abst.
DS	A4	JP	10-312971	A	NEC CORP.	11-24-1998		Abst.
DS	A5	JP	63-188983	A	RICOH CO., LTD., ET AL.	08-04-1988		Abst.

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>6</sup>
DS	A6	Ok-Hyun Nam et al., "Lateral Epitaxy of Low Defect Density GaN Layers via Organometallic Vapor Phase Epitaxy", Appl. Phys. Lett. 71 (18), 3 November 1997, pages 2638-2640.	
DS	A7	M. Kuramoto et al., "Room-Temperature Continuous-Wave Operation of InGaN Multi-Quantum-Well Laser Diodes Grown on an n-GaN Substrate with a Backside n-Contact", Jpn. J. Appl. Phys., Vol. 38, (1999), pages L184 -L186.	
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<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

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